



US00D428859S

# United States Patent [19]

Kawafuji et al.

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[54] SEMICONDUCTOR DEVICE

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[73] Assignee: Mitsubishi Denki Kabushiki Kaisha, Tokyo, Japan

[\*\*] Term: 14 Years

[21] Appl. No.: 29/106,586

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### [30] Foreign Application Priority Data

Jan. 28, 1999 [JP] Japan ..... 11-1841

[51] LOC (7) Cl. .... 13-03

[52] U.S. Cl. .... D13/182

[58] Field of Search ..... D13/182; 174/52.1, 174/52.4; 439/55; 361/718, 820

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### [57] CLAIM

The ornamental design for a semiconductor device, as shown and described.

### DESCRIPTION

FIG. 1 is a front elevational view of a semiconductor device, showing our new design;  
 FIG. 2 is a rear elevational view thereof;  
 FIG. 3 is a top plan view thereof;  
 FIG. 4 is a bottom plan view thereof;  
 FIG. 5 is a left side elevational view thereof;  
 FIG. 6 is a right side elevational view thereof;  
 FIG. 7 is a cross-sectional view thereof, taken along line 7—7 in FIG. 1;  
 FIG. 8 is a cross-sectional view thereof, taken along line 8—8 in FIG. 1; and,  
 FIG. 9 is a front, right side and bottom perspective view thereof.

1 Claim, 6 Drawing Sheets

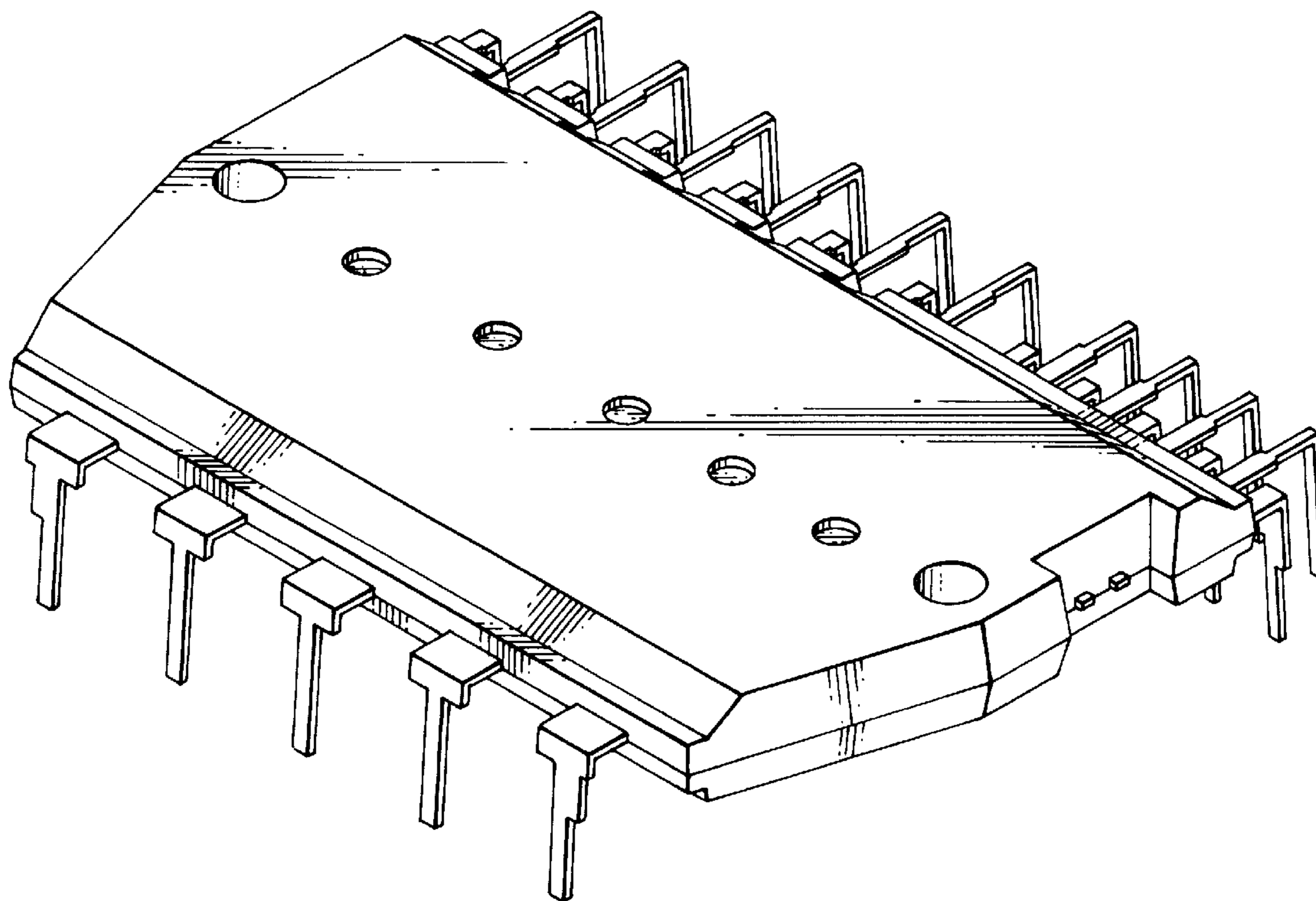


FIG. 1

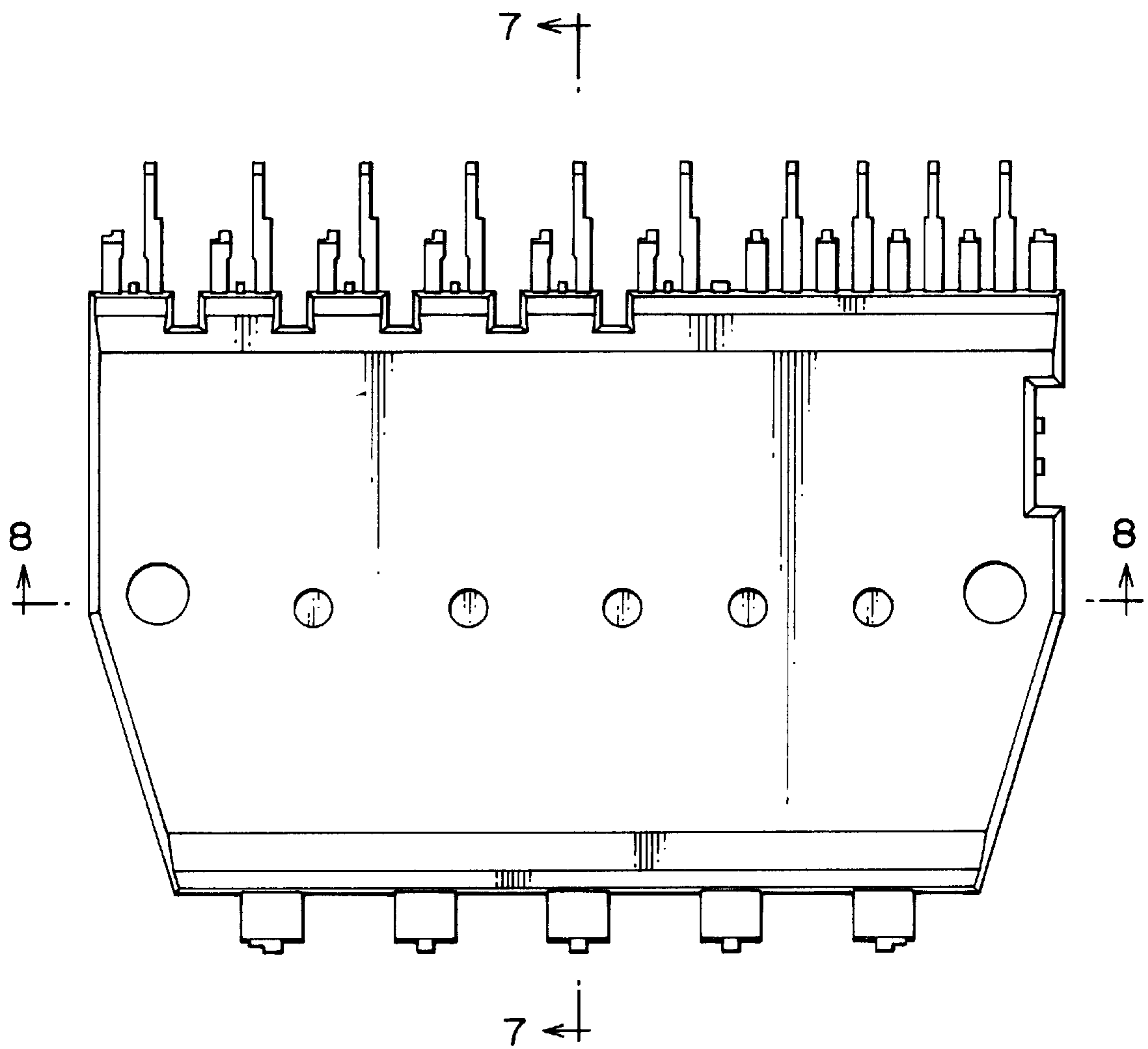


FIG. 2

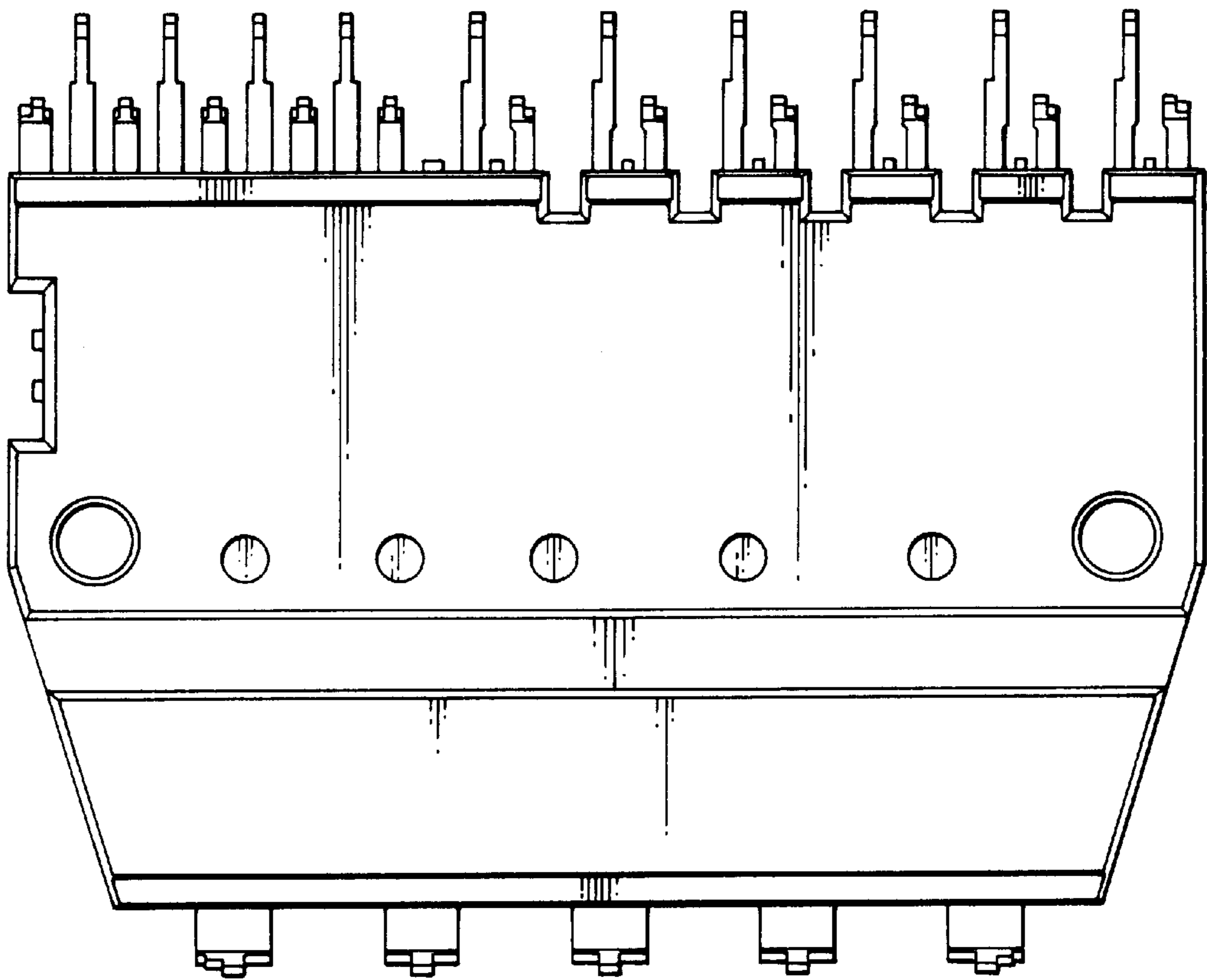


FIG. 3

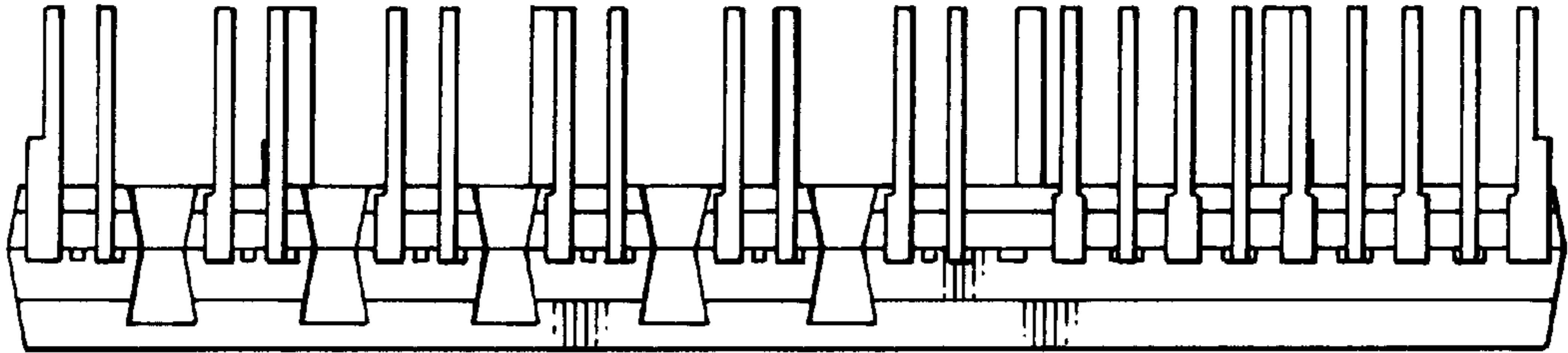


FIG. 4

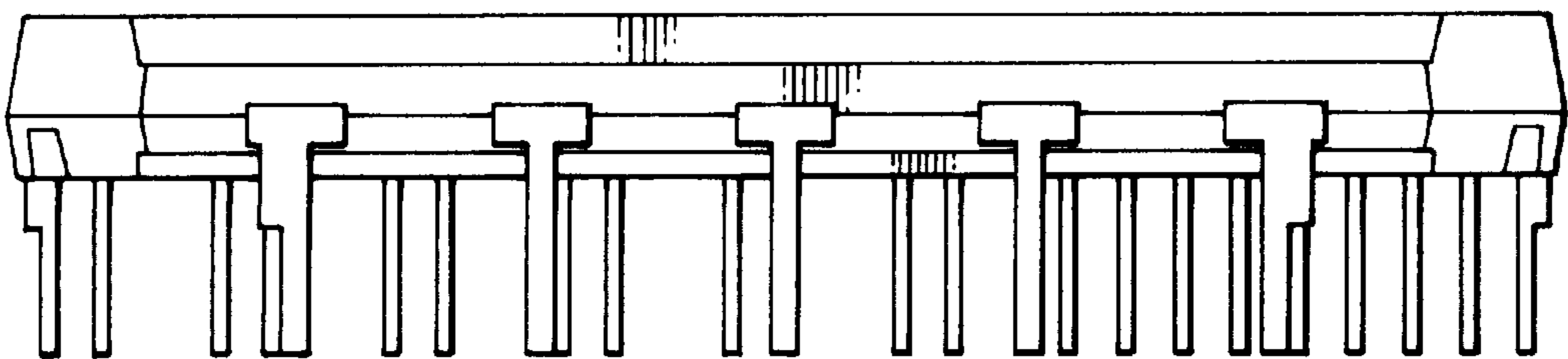


FIG. 5

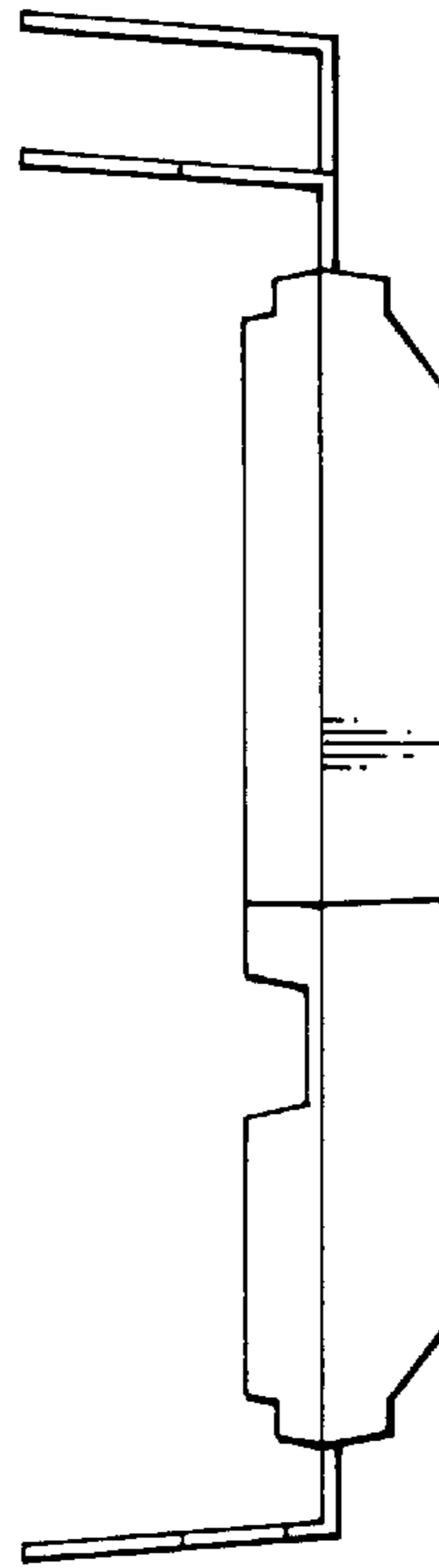


FIG. 6

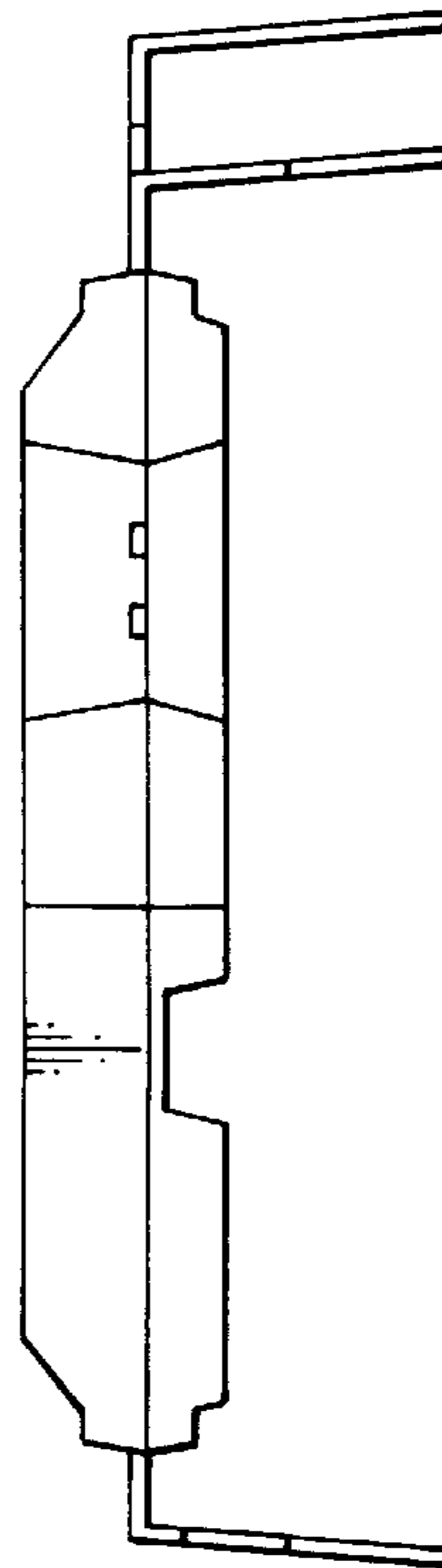


FIG. 7

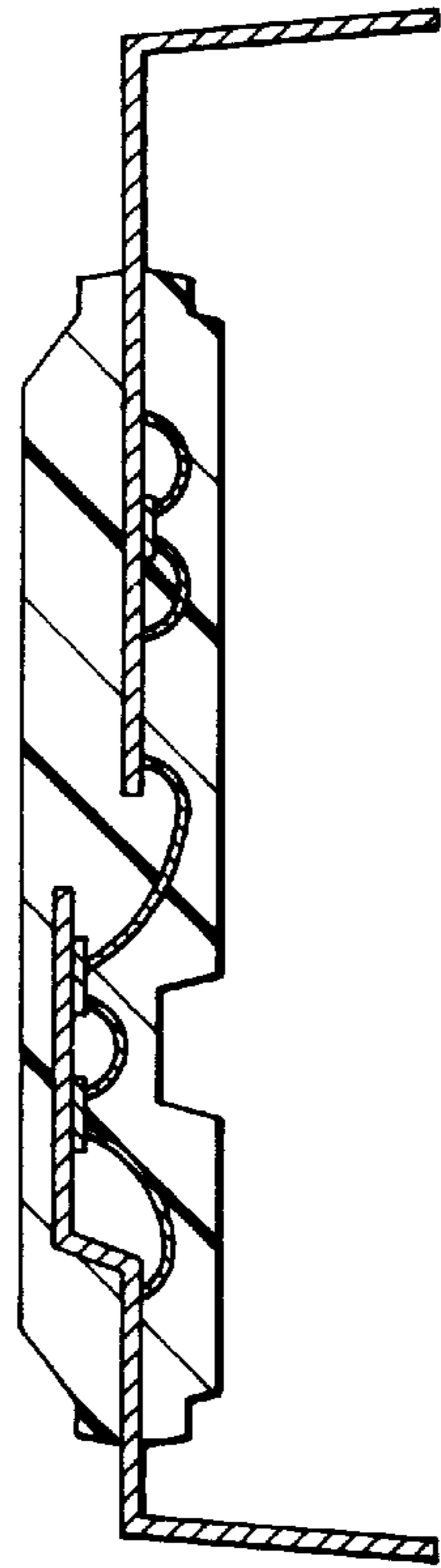


FIG. 8

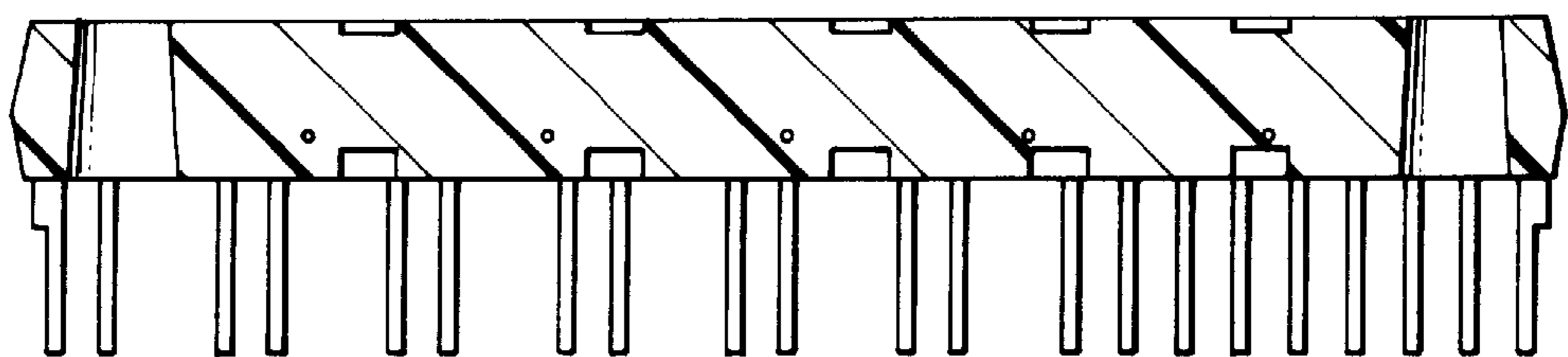


FIG. 9

